Dual 4-Input Data Selector/Multiplexer

High-Performance Silicon-Gate CMOS

The MC74HC153 is identical in pinout to the LS153. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The Address Inputs select one of four Data Inputs from each multiplexer. Each multiplexer has an active-low Strobe control and a noninverting output.

The HC153 is similar in function to the HC253, which has 3-state outputs.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- These are Pb-Free Devices

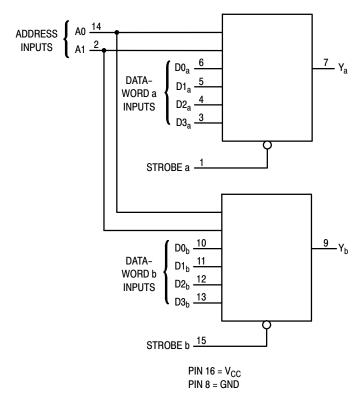
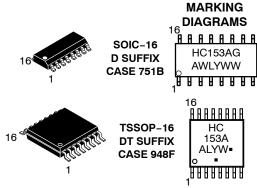


Figure 1. Logic Diagram



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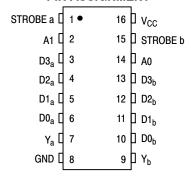


A = Assembly Location

WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or = Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT



FUNCTION TABLE

	Output			
A1	A1 A0 Strobe			
Х	Х	Н	L	
L	L	L	D0	
L	Н	L	D1	
Н	L	L	D2	
Н	Н	L	D3	

D0, D1, D2, and D3 = the level of the respective data input.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V _{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to + 7.0	V	
V _{in}	DC Input Voltage (Referenced to GND)	-1.5 to V _{CC} + 1.5	V	
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	V	
I _{in}	DC Input Current, per Pin	±20	mA	
I _{out}	DC Output Current, per Pin	±25	mA	
I _{CC}	DC Supply Current, V _{CC} and GND Pins		±50	mA
P _D	•	Package Package	500 TBD	mW
T _{stg}	Storage Temperature		-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or $V_{\rm CC}$). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Reference	0	V _{CC}	V	
T _A	Operating Temperature, All Package Types	-55	+125	°C	
t _r , t _f	(Figure 2)	$V_{CC} = 2.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V _{CC} V	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V _{IL}	Maximum Low-Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	0.3 0.9 1.2	0.3 0.9 1.2	0.3 0.9 1.2	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{in} = V_{IH} \text{ or } V_{IL} $ $ I_{out} \le 4.0 \text{ mA}$ $ I_{out} \le 5.2 \text{ mA}$	4.5 6.0	3.98 5.48	3.84 5.34	3.70 5.20	
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL} $ $ I_{out} \le 4.0 \text{ mA}$ $ I_{out} \le 5.2 \text{ mA}$	4.5 6.0	0.26 0.26	0.33 0.33	0.40 0.40	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	8	80	160	μΑ

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

			Gu			
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input D to Output Y (Figures 2 and 5)	2.0 4.5 6.0	140 28 24	175 35 30	210 42 36	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 3 and 5)	2.0 4.5 6.0	175 35 30	220 44 37	265 53 45	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Strobe to Output Y (Figures 4 and 5)	2.0 4.5 6.0	95 19 16	120 24 20	145 29 25	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 2 and 5)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
C _{in}	Maximum Input Capacitance	_	10	10	10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Multiplexer)	31	pF

SWITCHING WAVEFORMS

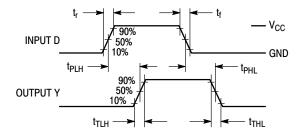


Figure 2.

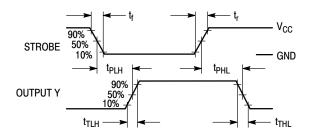


Figure 4.

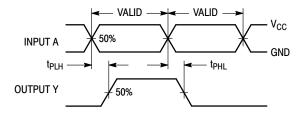
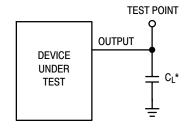


Figure 3.



^{*}Includes all probe and jig capacitance

Figure 5. Test Circuit

PIN DESCRIPTIONS

DATA INPUTS

D0_a - D3_a, D0_b - D3_b (Pins 3, 4, 5, 6, 10, 11, 12, 13)

Data Inputs. With the outputs enabled, the addressed Data Inputs appear at the Y outputs.

CONTROL INPUTS

A0, A1 (Pins 2, 14)

Address Inputs. These inputs address the pair of Data Inputs which appear at the corresponding outputs.

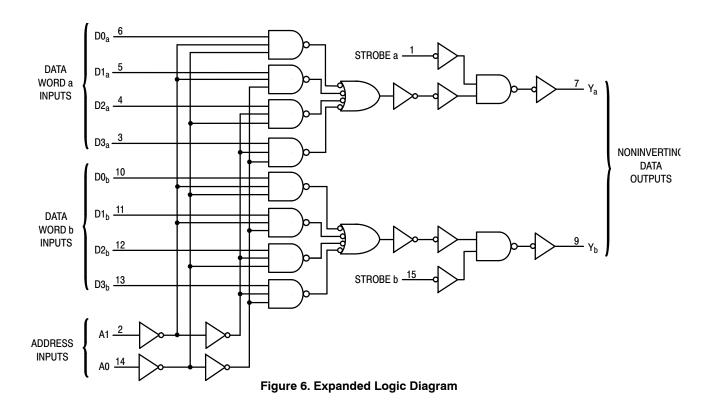
Strobe (Pins 1, 15)

Active-low Strobe. A low level applied to these pins enables the corresponding outputs.

OUTPUTS

Y_a, Y_b (Pins 7, 9)

Noninverting data outputs.



ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC153ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC153ADR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74HC153ADTR2G	TSSOP-16*	2500 Tape & Reel
MC74HC153ADTG	TSSOP-16*	96 Units / Tube

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
P	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
	COLLECTOR		CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DY		
2.	BASE		ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4		
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE		CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER		ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION		NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER		CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3		
13.	BASE		CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	SOI DEE	RING FOOTPRINT
14.	COLLECTOR		NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDER	IIIIG FOOTFRINT
15.	EMITTER			15.	EMITTER, #4	15.	BASE, #1		8X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1	—	— 6.40 — >
									0.10
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12 ✓ ➤
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPUT	7)		. \Box 1	16
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPUT			, — ·	
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	,			
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPUT	7)		16X 🛣	
6.	DRAIN, #3		CATHODE	6.	COMMON DRAIN (OUTPUT			.58 J	' <u> </u>
7.	DRAIN, #4		CATHODE	7.	COMMON DRAIN (OUTPUT		U		1
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT	7)			
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPUT				
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPUT				
13.	GATE, #2	13.	ANODE	13.	GATE N-CH	,			
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPUT	7)			— ↓ PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPUT				<u> </u>
16.	SOURCE, #1		ANODE	16.	SOURCE N-CH	,			
	/""		-					□ ₈	9 +
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									DIMENSIONS: MILLIMETERS

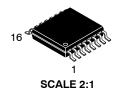
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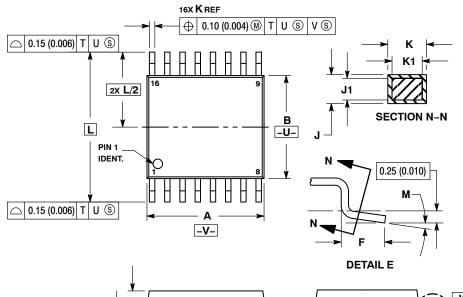
D

-T- SEATING PLANE



TSSOP-16 CASE 948F-01 ISSUE B

DATE 19 OCT 2006



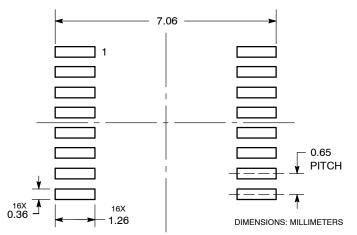
NOTES

- JIES:
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 ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD
 FLASH. PROTRUSIONS OR GATE BURRS.
 MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
C		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
7	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
Ы	6.40 BSC		0.252 BSC		
М	0 °	8 °	0 °	8 °	

SOLDERING FOOTPRINT

G



GENERIC MARKING DIAGRAM*

168888888 XXXX XXXX **ALYW** 188888888

XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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